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General purpose transistor (isolated transistor and diode)

EML20

DTC123J A and RB521S-30 are housed independently in a EMT6 package.

Applications

DC / DC converter Motor driver

Features

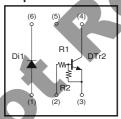
- Tr : NPN digital transistor
 Low V_F
- 2) Mounting possible with EMT3 automatic mounting machines.

Structure

NPN Silicon epitaxial planar digital transistor Schottky barrier diode

The following characteristics apply to both Di1 and DTr2.

●Equivalent circuit

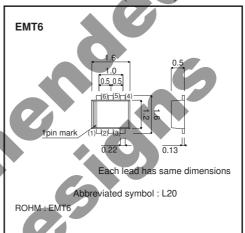


 $R_1=2.2k\Omega$, $R_2=47k\Omega$

Packaging specifications

Туре	EML20
Package	EMT6
Marking	L20
Code	T2R
Basic ordering unit (pieces)	8000

●External dimensions (Unit: mm)



● Absolute maximum ratings (Ta=25°C)

Di1

Parameter	Symbol	Limits	Unit
Average revtified forward current	lo	200	mA
Forward current surge peak (60Hz, 1∞)	IFSM	1	Α
Reverse voltage (DC)	VR	30	V
Junction temperature	Tj	125	°C

DTr2

Parameter	Symbol	Limits	Unit	
Supply voltage	Vcc	50	V	
Innut voltage	VIN	12	V	
Input voltage	VIN	-5		
Output ourront	lo	100	mA	
Output current	Ic (MAX.)	100	mA	
Power dissipation	Pd	120	mW *	
Junction temperature	Tj	150	°C	

^{*} Each terminal mounted on a recommended.

Di1/DTr2

Parameter	Symbol	Limits	Unit
Power dissipation	Pd	150	mW *
Storage temperature	Tstg	-55 to +125	°C

 * Each terminal mounted on a recommended.

●Electrical characteristics (Ta=25°C)

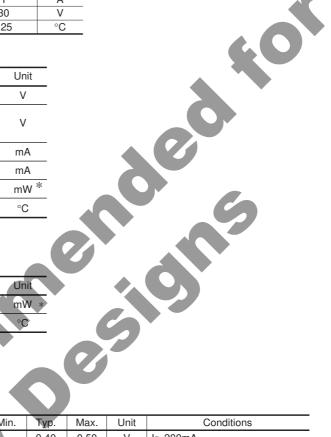
Di1

Paramete	er	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage		VF	—	0.40	0.50	V	I=200mA
Reverse current		lr 💮	1	4.0	30	μΑ	V _R =10V

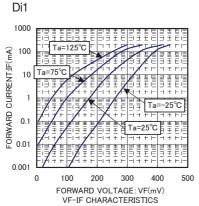
DTr2

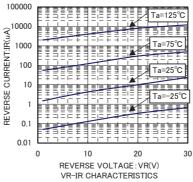
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Insultivellege	VI(off)	_	_	0.5	V	Vcc=5V / Io=100uA
Input voltage	VI(on)	1.1	_	_	V	Vo=0.3V / Io=5mA
Output voltage	Vo(on)	_	100	300	mV	lo=5mA, l≔0.25mA
Input current	II	_	_	3.6	mA	V=5V
Output current	IO(off)	_	-	500	nA	Vcc=50V / Vi=0V
DC current gain	Gı	80	-	_	_	Vo=5V / Io=10mA
Transition frequency *	f⊤	_	250	_	MHz	Vc=10V / I=-5mA, f=100MHz
Input resistance	R ₁	1.54	2.2	2.86	kΩ	_
Resistance ratio	R ₂ /R ₁	17	21	26	_	_

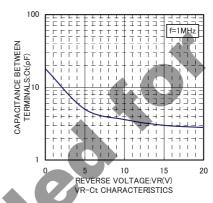
^{*} Characteristics of built-in transistor.



•Electrical characteristic curves







DTr2

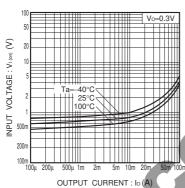


Fig.1 Input voltage vs. output current (ON characteristics)

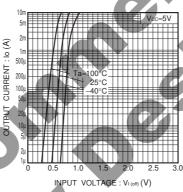


Fig.2 Output current vs. input voltage (OFF characteristics)

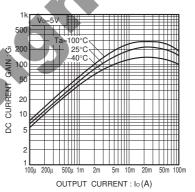


Fig.3 DC current gain vs. output current

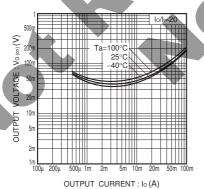


Fig.4 Output voltage vs. output current

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